OIP E 422

Attorney Docket No. 0756-7218

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

atent Application of:

) Group Art Unit: 2826

Shunpei YAMAZAKI et al.

) Examiner: Fetsum Abraham

Serial No. 10/712,062

) CERTIFICATE OF MAILING

Filed: November 14, 2003

' I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450,

For: SEMICONDUCTOR DEVICE AND

Commissioner for Patents, P.O. Box 145
Alexandria, VA 22313-1450, on 2.8.06
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METHOD OF FABRICATING SAME

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing information known to Applicant and requests that this information be made of record in the above identified application. Copies are submitted herewith in accordance with 37 C.F.R. 1.98(a).

Copies of U.S. patents and U.S. publications are not enclosed in accordance with the Notice published in the Official Gazette on August 5, 2003 entitled *Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003*, which waives the requirement under 37 CFR 1.98(a)(2)(i) for submitting a copy of each cited U.S. patent and each U.S. publication.

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

Respectfully submitted,

Eric J. Robinson Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C. PMB 955

21010 Southbank Street Potomac Falls, Virginia 20165

(571) 434-6789

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Complete if Known Substitute for form 1449A/PTO Application Number 10/712,062 INFORMATION DISCLOSURE November 14, 2003 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named Inventor (use as many sheets as necessary) **Group Art Unit** 2826 Examiner Name Feisum Abraham Benjamin T Liu of Attorney Docket Number Sheet 1 0756-7218

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						U.S. PATENT DOC	UMEN1	s				
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Examiner Signature		/Ben	amin Tzu-Hur	g Liu/			Date Consi	dered	05/	01/2	008	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Attorney Docket No. 0756-7218

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)	Group Art Unit: 2826
Shunpei YAMAZAKI et al.)	Examiner: Fetsum Abraham
Serial No. 10/712,062)	CERTIFICATE OF MAILING I hereby certify that this correspondence is
Filed: November 14, 2003)	being deposited with the United States Postal Service with sufficient postage as First Class
For: SEMICONDUCTOR DEVICE AND)	Mail in an envelope addressed to:
METHOD OF FABRICATING SAME)	Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on 2-8-06.

CORRECTION TO PREVIOUSLY SUBMITTED INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

It has come to applicant's attention that an Information Disclosure Statement previously submitted included inadvertent typographical errors or incomplete information.

Specifically, the Information Disclosure Statement filed November 14, 2003 included the following inaccuracies:

- 1) U.S. Patent 4,330,363 was incorrectly listed with the inventor as Biefesen et al. The correct inventor should be Biegesen et al.;
- 2) U.S. Patent 4,996,077 was incorrectly listed with the inventor as Mosiehi et al. The correct inventor should be Moslehi et al.
- 3) U.S. Patent No. 5,089,441 is incorrected lised with the inventor as Mosiehi et al. The correct inventor should be Moslehi et al.
- 4) EP 0 178 447 was incorrectly listed with a publication date of 10/09/84. The correct publication date is 04/23/1986.
- 5) The article to Kruper et al. did not include the volume and number. The corrected citation should read: Kuper et al., "Effects of Fluorine Implantation on the

Kinetics of Dry Oxidation of Silicon," Volume 60, No. 3, August 1, 1986, pp. 985-990, J. Applied Physics.

- The article to Nemanich et al. incorrectly lists the volume. The correct volume number is 23.
- 7) The article to Wolf et al. did not include the volume. The corrected citation should read: Wolf et al., "Thermal Oxidation of Single Crystal Silicon," <u>Volume 1</u>, 1986, pp. 207-211, Silicon Processing for the VLSI Era.
- 8) The article to Dvurechenskii et al. did not include the volume. The corrected citation should read: Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Volume 95, 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR.
- The article to Hayzelden et al. incorrectly lists the date as May 15, 1993.
 The correct date is June 1, 1993.
- 10) Page 5 and 10 of the Information Disclosure Statement have been initialed by the Examiner and dated "8/30/01." The subject application was filed on November 14, 2003, and therefore the date of review of incorrect. Copies are enclosed.

The above inaccuracies are corrected on the 1449 Form attached hereto. This Correction to Previously Submitted Information Disclosure Statements is being submitted herewith with an Information Disclosure Statement, RCE, and requisite fee. The Examiner is requested to initial the attached PTO Form 1449 evidencing consideration of the above references and line through these references on the previously submitted Information Disclosure Statements to ensure that the correct information is printed correctly on any issued patent.

Respectfully submitted,

Eric J. Robinson Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, Virginia 20165 (571) 434-6789 Please type a plus sign (+) \$\int_{\text{Side}} \text{this box → Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

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Complete if Known Substitute for form 1449A/PTO Application Number 10/712.062 INFORMATION DISCLOSURE November 14, 2003 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named inventor (use as many sheets as necessary) Group Art Unit Felsum Abrehem Benjamin T. Liu Examiner Name of Attorney Docket Number 0756-7218 Sheet U.S. PATENT DOCUMENTS U.S. Petent Document Dete of Publication of Cited Peges, Columns, Lines, Where nt Pessages or Rele Figures Appear Initials Name of Patentee or Applicant of MM-DD-YYYY Cited Document Number Kind Code³ /BTL 4,330,363 Biegesen et al. 05/18/1982 02/26/1991 4,996,077 Moslehi et al. 5 089 441 Moslehi 02/18/1992 FOREIGN PATENT DOCUMENTS Foreign Petent Document Date of Publication of Cited Peges, Columns, Lines, Where Relevant Pesseges Examine Initiels Document MM-DD-YYYY Kind Code⁵ Applicant of Cited Document or Relevent Figures Appo Number⁴ (if known) Office² 04/23/1986 /BTL/ EP 0 178 447 Eng. OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Examiner Initials T^2 item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.

Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," Volume 60, No. 3, August 1, 1986, pp. 985-990, J. Applied Physics. /BTL/ Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 23, No. 12. Wolf et al., "Thermal Oxidation of Single Crystal Silicon," Volume 1, 1986, pp. 207-211, Silicon Processing for the VLSI Era. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Volume 95, 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR, Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," June 1, 1993, pp. 8279-8289, J. Appl. Phys. 73(12) Date 05/01/2008 Examiner /Benjamin Tzu-Hung Liu/ Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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				Examiner Name	Fetsum Abraham
Sheet	5	of	12	Attorney Docket Number	0756-7218

				U.S. PATENT DOCUMEN	rs		
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			U.S. PATENT DOCUMEN	TS		
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